

FFSP0665B

Silicon Carbide Schottky Diode

650 V, 6 A

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 26 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuit

ABSOLUTE MAXIMUM RATINGS

(T_C = 25°C, Unless otherwise specified)

Symbol	Parameter	Value	Unit	
V _{RRM}	Peak Repetitive Reverse Voltage	650	V	
E _{AS}	Single Pulse Avalanche Energy (Note 1)	26	mJ	
I _F	Continuous Rectified Forward Current @ T _C < 150°C	6.0	A	
	Continuous Rectified Forward Current @ T _C < 135°C	8.0		
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	473	A
		T _C = 150°C, 10 μs	408	
I _{F, SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	28	A
P _{tot}	Power Dissipation	T _C = 25°C	49	W
		T _C = 150°C	8.3	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

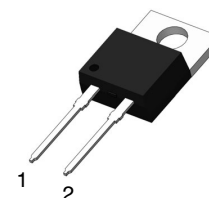
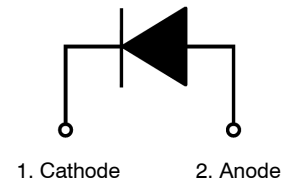
1. E_{AS} of 26 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 10.2 A, V = 50 V.



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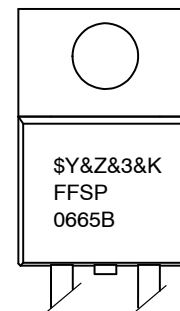
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ELECTRICAL CONNECTION



TO-220-2LD
CASE 340BB

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
 &Z = Assembly Plant Code
 &3 = Numeric Date Code
 &K = Lot Code
 FFSP0665B = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.46	$^{\circ}C/W$

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSP0665B	FFSP0665B	TO220	Tube	N/A	N/A	50 Units

ELECTRICAL CHARACTERISTICS $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_F	Forward Voltage	$I_F = 6\text{ A}, T_C = 25^{\circ}C$		1.38	1.7	V
		$I_F = 6\text{ A}, T_C = 125^{\circ}C$		1.6	2.0	
		$I_F = 6\text{ A}, T_C = 175^{\circ}C$		1.72	2.4	
I_R	Reverse Current	$V_R = 650\text{ V}, T_C = 25^{\circ}C$		0.025	40	μA
		$V_R = 650\text{ V}, T_C = 125^{\circ}C$		0.08	80	
		$V_R = 650\text{ V}, T_C = 175^{\circ}C$		0.22	160	
Q_C	Total Capacitive Charge	$V = 400\text{ V}$		15		nC
C	Total Capacitance	$V_R = 1\text{ V}, f = 100\text{ kHz}$		259		pF
		$V_R = 200\text{ V}, f = 100\text{ kHz}$		29		
		$V_R = 400\text{ V}, f = 100\text{ kHz}$		23		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

$T_J = 25^\circ\text{C}$ Unless Otherwise Noted

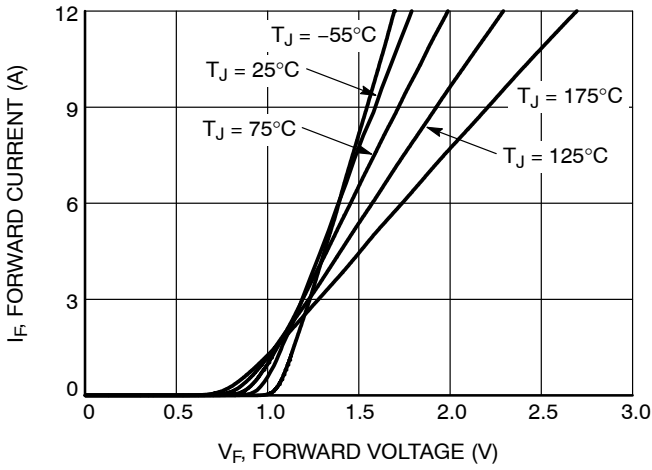


Figure 1. Forward Characteristics

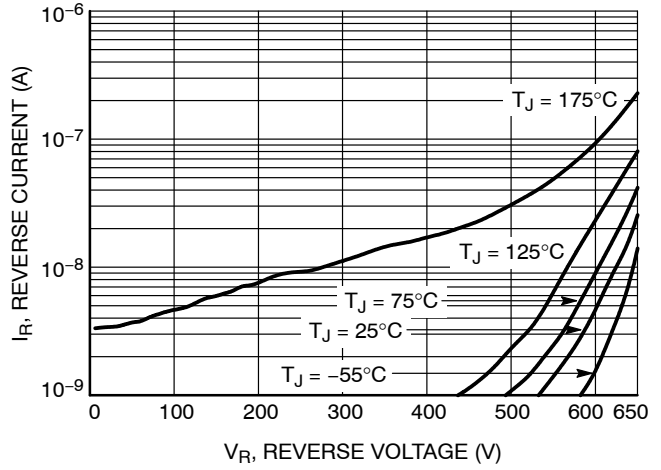


Figure 2. Reverse Characteristics

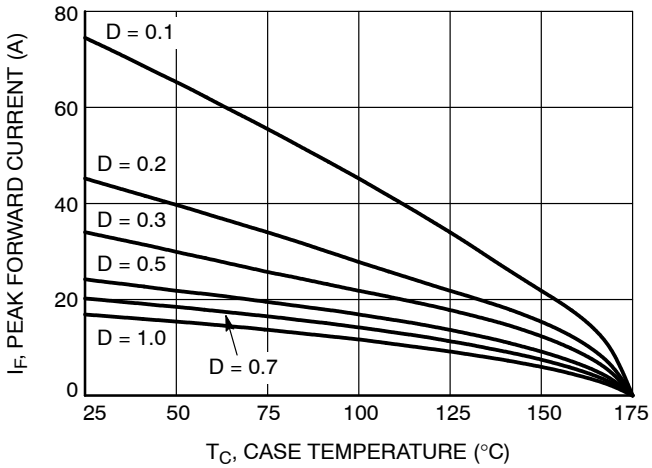


Figure 3. Current Derating

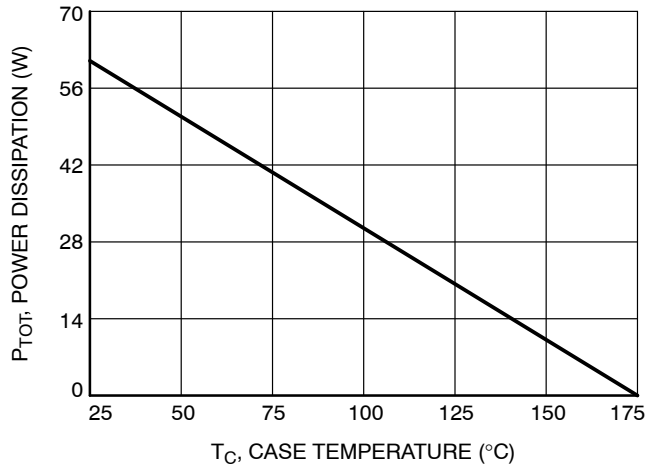


Figure 4. Power Dissipation

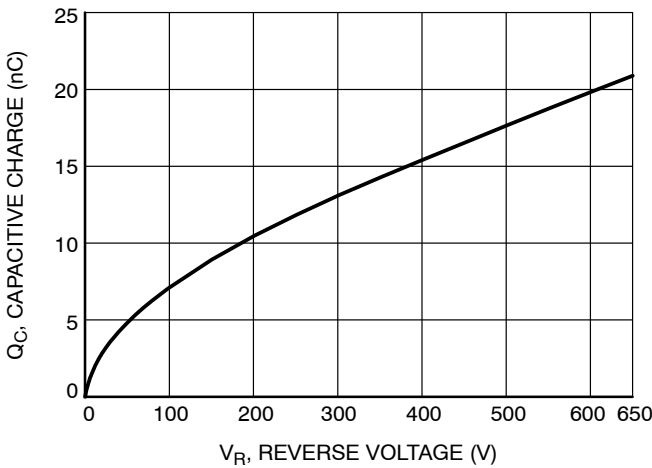


Figure 5. Capacitance Charge vs. Reverse Voltage

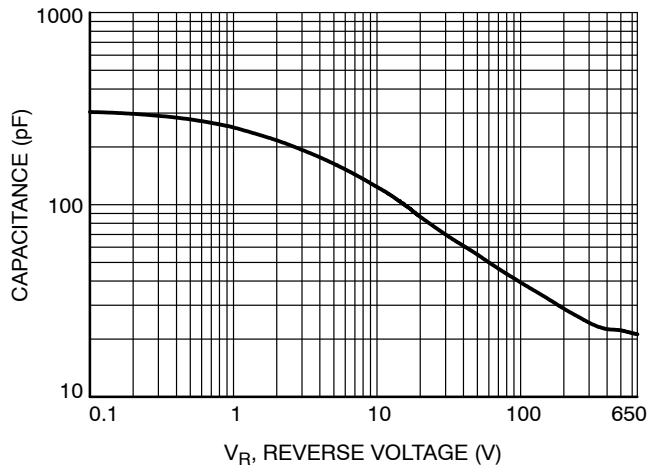


Figure 6. Capacitance vs. Reverse Voltage

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TYPICAL CHARACTERISTICS

T_J = 25°C Unless Otherwise Noted (continued)

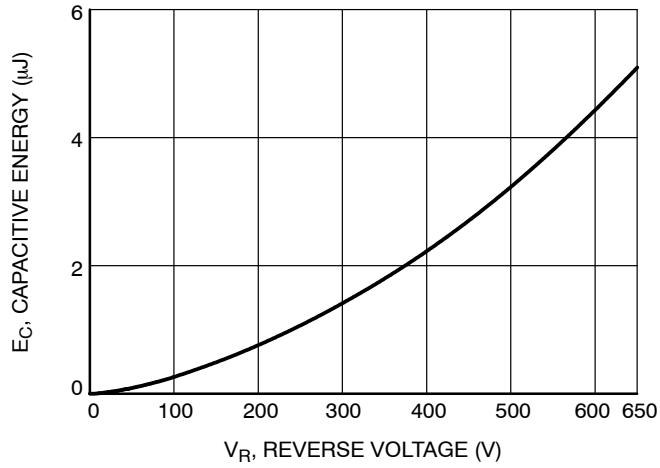


Figure 7. Capacitance Stored Energy

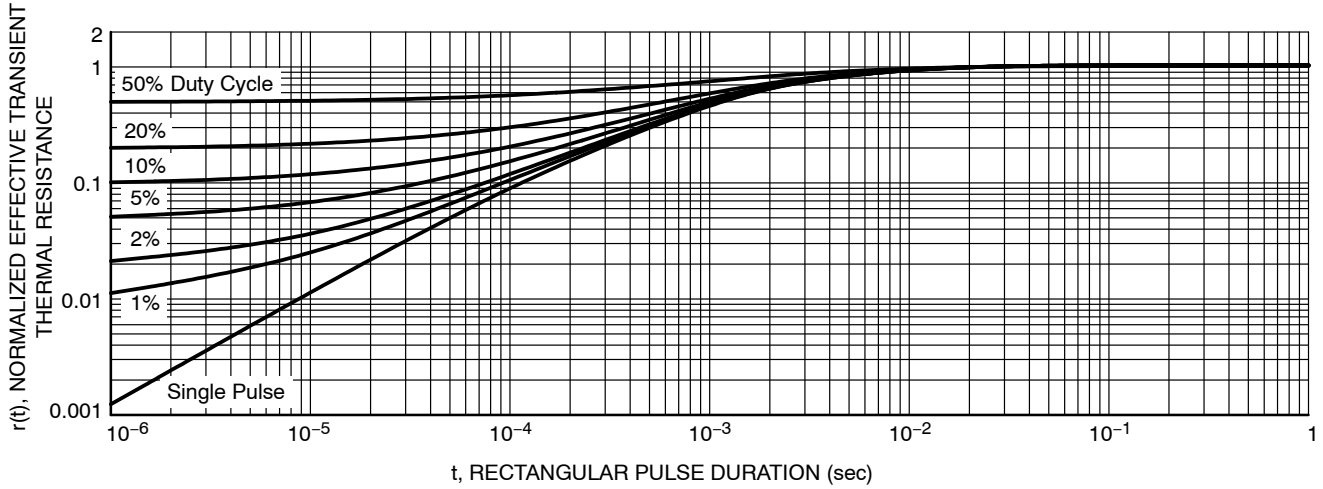


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

L = 0.5 mH
R < 0.1Ω

V_{DD} = 50V

$E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$

Q1 = IGBT (BV_{CES} > DUT V_{R(AVL)})

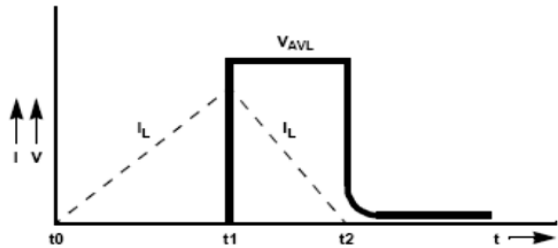
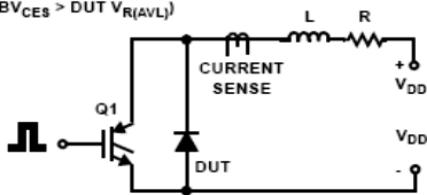


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

